



MH173 Specifications

High Sensitivity Built-in Pull High Res Hall Effect Latch

MH173 Hall-effect sensor is a temperature stable, stress-resistant sensor. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

MH173 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, Pull-up resistor output. Advanced DMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

This device requires the presence of both south and north polarity magnetic fields for operation. In the presence of a south polarity field of sufficient strength, the device output sensor on, and only switches off when a north polarity field of sufficient strength is present.

MH173 is rated for operation between the ambient temperatures -40°C and 85°C for the E temperature range, and -40°C to 125°C for the K temperature range. The package style available provide magnetically optimized solutions for most applications. Package SO is an SOT-23, a miniature low-profile surface-mount package.

Packages is Halogen Free standard and which have been verified by third party lab.

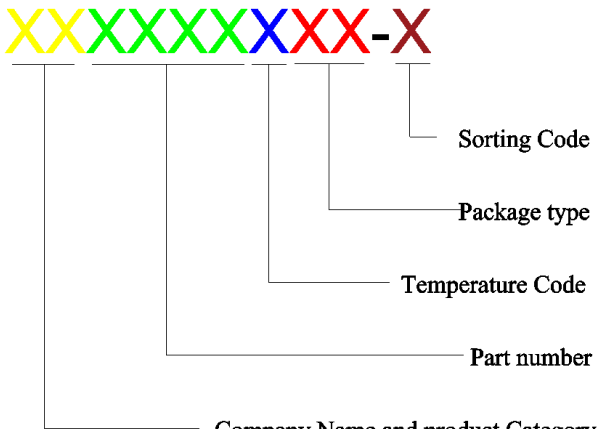
Features and Benefits

- DMOS Hall IC Technology
- Chopper stabilized amplifier stage.
- Optimized for BLDC motor applications.
- Reliable and low shifting on high Temp condition.
- Switching offset compensation at typically 69kHz
- Pull-up resistor output
- Good ESD Protection.
- 100% tested at 125°C for K.
- Custom sensitivity / Temperature selection are available.
- Reverse bias protection on power supply pin.
- RoHS compliant 2011/65/EU and Halogen Free

Applications

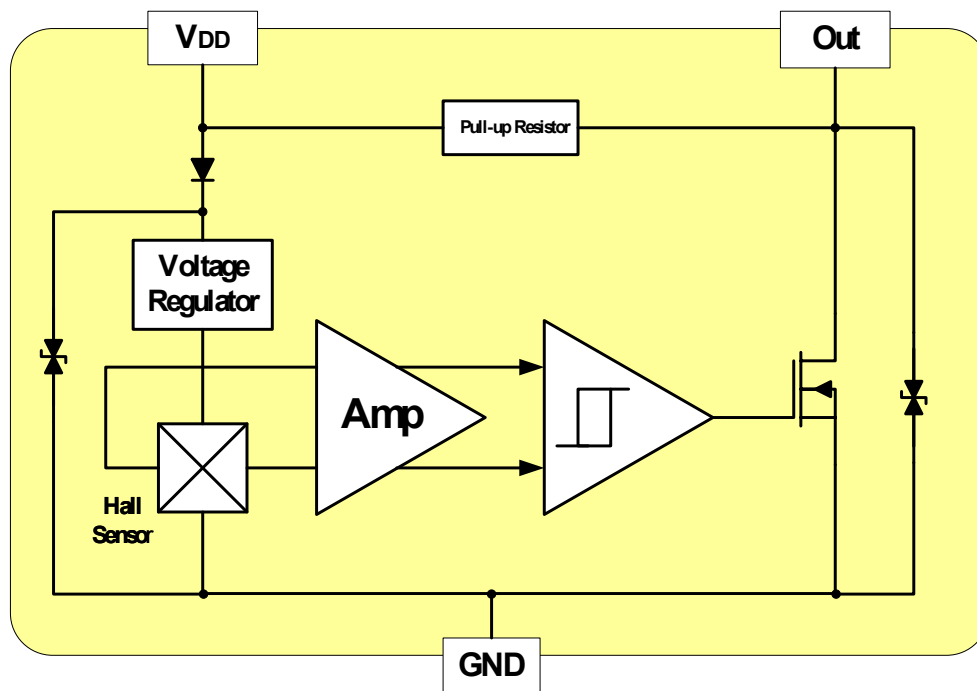
- High temperature Fan motor
- 3 phase BLDC motor application
- Speed sensing
- Position sensing
- Current sensing
- Revolution counting
- Solid-State Switch
- Linear Position Detection
- Angular Position Detection
- Proximity Detection
- High ESD Capability

Ordering Information

| | |
|---|---|
|  | <p>Company Name and Product Category MH:MST Hall Effect/MP:MST Power IC</p> <p>Part number 181,182,183,184,185,248,249,276,477,381,381F,381R,382..... If part # is just 3 digits, the forth digit will be omitted.</p> <p>Temperature range E: 85 °C, I: 105 °C, K: 125 °C, L: 150 °C</p> <p>Package type UA:TO-92S,VK:TO-92S(4pin),VF:TO-92S(5pin),SO:SOT-23, SQ:QFN-3,ST:TSOT-23,SN:SOT-553,SF:SOT-89(5pin), SS:TSOT-26,SD:DFN-6</p> <p>Sorting α,β,Blank.....</p> |
|---|---|

| Part No. | Temperature Suffix | Package Type |
|----------|----------------------|--------------|
| MH173KSO | K (-40°C to + 125°C) | SO (SOT-23) |
| MH173ESO | E (-40°C to + 85°C) | SO (SOT-23) |

Functional Diagram



Absolute Maximum Ratings At ($T_a=25\text{ }^\circ\text{C}$)

| Characteristics | | Values | Unit |
|---|----------------------|-------------|--------------------|
| Supply voltage, (V_{DD}) | | 28 | V |
| Output Voltage, (V_{out}) | | 28 | V |
| Reverse Voltage, (V_{DD} / V_{out}) | | -0.3 | V |
| Output current, (I_{SINK}) | | 25 | mA |
| Operating Temperature Range, (T_A) | "E" Class | -40 ~ +85 | $^\circ\text{C}$ |
| | "K" Class | -40 ~ +125 | $^\circ\text{C}$ |
| Storage temperature range, (T_S) | | -65 to +150 | $^\circ\text{C}$ |
| Maximum Junction Temp, (T_J) | | 150 | $^\circ\text{C}$ |
| Thermal Resistance | (θ_{JA}) SO | 543 | $^\circ\text{C/W}$ |
| | (θ_{JC}) SO | 410 | $^\circ\text{C/W}$ |
| Package Power Dissipation, (P_D) SO | | 230 | mW |

Note: Do not apply reverse voltage to V_{DD} and V_{OUT} Pin, It may be caused for Miss function or damaged device.

Electrical Specifications

DC Operating Parameters : $T_A=+25\text{ }^\circ\text{C}$, $V_{DD}=12\text{V}$

| Parameters | Test Conditions | Min | Typ | Max | Units |
|--|---|-----|-----|-------|---------------|
| Supply Voltage, (V_{DD}) | Operating | 2.5 | | 26 | V |
| Supply Current, (I_{DD}) | $B < B_{OP}$ | | 3.0 | 5.0 | mA |
| Output Saturation Voltage, (V_{sat}) | $B > B_{OP}$ | | | 400.0 | mV |
| Output Leakage Current, (I_{off}) | I_{OFF} $B < B_{RP}$, $V_{OUT} = 12\text{V}$ | | | 10.0 | μA |
| Output Rise Time, (T_R) | $R_L=1.1\text{K}\Omega$, $C_L=20\text{pF}$ | | | 0.45 | μs |
| Output Fall Time, (T_F) | $R_L=820\Omega$; $C_L=20\text{pF}$ | | | 0.45 | μs |
| Electro-Static Discharge | HBM | 4 | | | KV |
| Operate Point, (BOP) | SO | 5 | | 60 | GS |
| Release Point, (BRP) | SO | -60 | | -5 | GS |
| Hysteresis, (BHYS) | $ BOP - BRP $ | | 60 | | GS |

Typical application circuit

